# PBYR2545CTB series

# **GENERAL DESCRIPTION**

# Dual low leakage, platinum barrier, schottky rectifier diodes in a plastic envelope suitable for surface mounting, featuring low forward voltage drop, absence of stored charge. and guaranteed reverse surge capability. The devices are intended for use in switched mode power supplies and high frequency circuits in general where low conduction and zero switching losses are important.

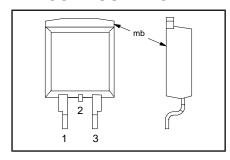
# **QUICK REFERENCE DATA**

SYMBOL	PARAMETER	MAX.	MAX.	MAX.	UNIT
V <sub>RRM</sub> V <sub>F</sub> I <sub>O(AV)</sub>	PBYR25- Repetitive peak reverse voltage Forward voltage Average output current (both diodes conducting)	35CTB 35 0.62 30	<b>40CTB</b> 40 0.62 30	<b>45CTB</b> 45 0.62 30	V V A

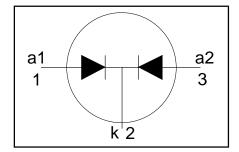
# **PINNING - SOT404**

PIN	DESCRIPTION
1	anode 1
2	cathode
3	anode 2
mb	cathode

# PIN CONFIGURATION



# **SYMBOL**



# LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.		MAX.		UNIT
V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	Repetitive peak reverse voltage Crest working reverse voltage Continuous reverse voltage	T <sub>mb</sub> ≤ 136 °C		<b>-35</b> 35 60 35	<b>-40</b> 40 80 40	<b>-45</b> 45 100 45	<<<
I <sub>O(AV)</sub>	Average output current (both diodes conducting)	square wave; $\delta = 0.5$ ; $T_{mb} \le 130 ^{\circ}\text{C}$	-		30		A
I <sub>O(RMS)</sub>	RMS output current (both diodes conducting)	- mb = 100 0	-		43		A
I <sub>FRM</sub>	Repetitive peak forward current per diode	$t = 25 \mu s$ ; $δ = 0.5$ ; $T_{mb} \le 130 °C$	-		30		A
I <sub>FSM</sub>	Non-repetitive peak forward current, per diode	t = 10 ms t = 8.3 ms sinusoidal $T_j$ = 125 °C prior to surge; with reapplied $V_{RRM(max)}$	-		135 150		A A
l <sup>2</sup> t	I <sup>2</sup> t for fusing	It = 10 ms	-		91		A <sup>2</sup> s
I <sub>RRM</sub>	Repetitive peak reverse current per diode.		-		1		A
I <sub>RSM</sub>	Non-repetitive peak reverse current per diode.	$t_{p} = 100 \ \mu s$	-		1		A
T <sub>stg</sub> T <sub>j</sub>	Storage temperature Operating junction temperature		-65 -		175 150		ů C

Rectifier	diodes
schottky	barrier

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# THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{\text{th j-mb}}$ $R_{\text{th j-a}}$	Thermal resistance junction to mounting base Thermal resistance junction to ambient	per diode both diodes minumum footprint, FR4 board	1 1 1	- - 50	1.5 1.0 -	K/W K/W K/W

# STATIC CHARACTERISTICS

 $T_i = 25$  °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V <sub>F</sub>	Forward voltage (per diode)	I <sub>F</sub> = 30 A; T <sub>j</sub> = 125°C I <sub>F</sub> = 20 A; T <sub>j</sub> = 125°C	-	0.65	0.73	V
			-	0.53	0.62	V
		$I_{\rm F} = 30 \text{ A}$	-	0.77	0.82	V
$ I_R $	Reverse current (per diode)	$V_R = V_{RRM}$	-	100	200	μΑ
		$V_{R} = V_{RRM}$ ; $T_{i} = 125  ^{\circ}C$	-	12	40	mΑ
C <sub>d</sub>	Junction capacitance (per diode)	$V_R = V_{RRM}^{NNM}$ ; $T_j = 125 ^{\circ}C$ $f = 1MHz$ ; $V_R = 5V$ ; $T_j = 25 ^{\circ}C$ to 125 $^{\circ}C$	-	800	-	pF

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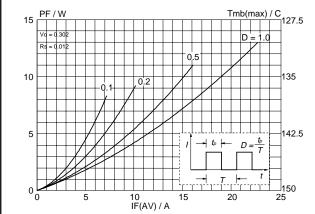


Fig.1. Maximum forward dissipation  $P_F = f(I_{F(AV)})$  per diode; square current waveform where  $I_{F(AV)} = I_{F(RMS)} x \sqrt{D}$ .

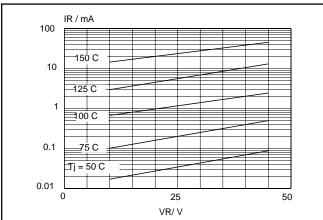


Fig.4. Typical reverse leakage current per diode;  $I_R = f(V_R)$ ; parameter  $T_j$ 

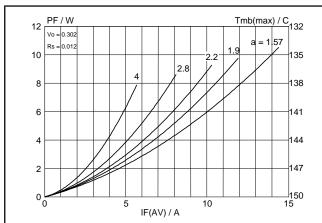


Fig.2. Maximum forward dissipation  $P_F = f(I_{F(AV)})$  per diode; sinusoidal current waveform where a = f form factor  $= I_{F(RMS)} / I_{F(AV)}$ .

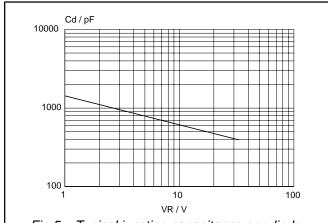


Fig.5. Typical junction capacitance per diode;  $C_d = f(V_R)$ ; f = 1 MHz;  $T_j = 25$ °C to 125 °C.

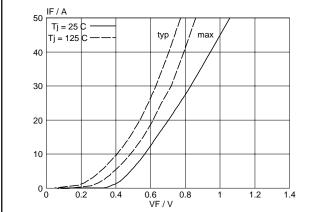


Fig.3. Typical and maximum forward characteristic  $I_F = f(V_F)$ ; parameter  $T_i$ 

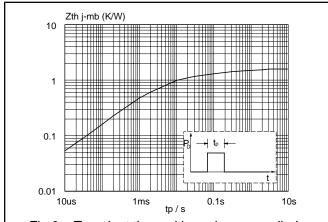
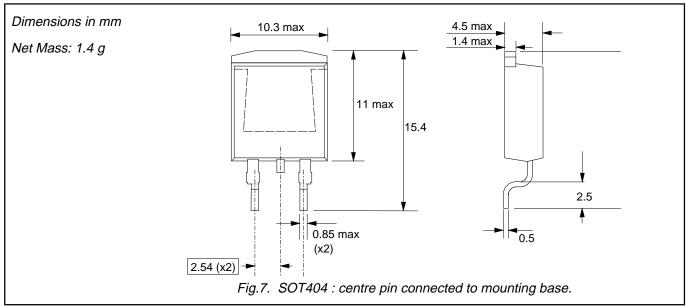


Fig.6. Transient thermal impedance per diode;  $Z_{th j-mb} = f(t_p)$ .

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# **MECHANICAL DATA**



## **Notes**

1. Epoxy meets UL94 V0 at 1/8".

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# **DEFINITIONS**

Data sheet status					
Objective specification	This data sheet contains target or goal specifications for product development.				
Preliminary specification This data sheet contains preliminary data; supplementary data may be published					
Product specification This data sheet contains final product specifications.					
Product specification	This data sheet contains final product specifications.				

## Limiting values

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

### **Application information**

Where application information is given, it is advisory and does not form part of the specification.

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